P-Channel 100-V (D-S) MOSFET

Key Features:

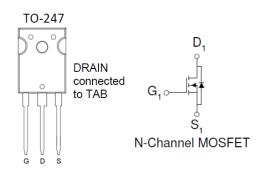
- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

Typical	Application	ons:
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- · White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY			
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I□ (A)	
-100	80 @ V _{GS} = -10V	-90 ^a	
-100	$85 @ V_{GS} = -4.5V$	-90	





ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	Limit	Units	
Drain-Source Voltage		V_{DS}	-100	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current a	T _C =25°C	I _D	-90	А	
Pulsed Drain Current ^b		I _{DM}	-360	^	
Continuous Source Current (Diode Conduction) a	T _C =25°C	I _S	-90	Α	
Power Dissipation ^a	T _C =25°C	P_{D}	500	W	
Operating Junction and Storage Temperature Range		T_J , T_{stg}	-55 to 175	°C	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Maximum	Units	
Maximum Junction-to-Ambient °	$R_{\theta JA}$	40	°C/W	
Maximum Junction-to-Case	$R_{\theta JC}$	0.29	C/VV	

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Notes

- a. Package Limited
- b. Pulse width limited by maximum junction temperature
- c. Surface Mounted on 1" x 1" FR4 Board.

Electrical Characteristics

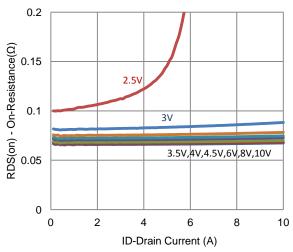
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-1			V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA
Zero Gate Voltage Drain Current	1	$V_{DS} = -80 \text{ V}, V_{GS} = 0 \text{ V}$			-1	uA
Zelo Gate Voltage Brain Current	I _{DSS}	$V_{DS} = -80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-10	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	-112.5			Α
Drain Cauras On Basistanas a	r	$V_{GS} = -10 \text{ V}, I_{D} = -20 \text{ A}$			80	mΩ
Drain-Source On-Resistance ^a	r _{DS(on)}	$V_{GS} = -4.5 \text{ V}, I_{D} = -18 \text{ A}$			85	11122
Forward Transconductance a	g _{fs}	$V_{DS} = -50 \text{ V}, I_{D} = -20 \text{ A}$		39		S
Diode Forward Voltage ^a	V_{SD}	$I_{S} = -45 \text{ A}, V_{GS} = 0 \text{ V}$		-1.1		V
		Dynamic ^b				
Total Gate Charge	Q_g	$V_{DS} = -50 \text{ V}, V_{GS} = -4.5 \text{ V},$		48		
Gate-Source Charge	Q_{gs}	$V_{DS} = -30 \text{ V}, V_{GS} = -4.3 \text{ V},$ $I_{D} = -2 \text{ A}$		14		nC
Gate-Drain Charge	Q_gd	10 - 2 A		13		
Turn-On Delay Time	t _{d(on)}	$V_{DS} = -50 \text{ V}, R_1 = 25 \Omega,$		15		
Rise Time	t _r	$V_{DS} = -50 \text{ V}, \ N_L = 25 \Omega,$ $I_D = -2 \text{ A},$		10		ne
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = -10 \text{ V}, R_{GEN} = 6 \Omega$		117		ns
Fall Time	t _f	V GEN - 10 V, T GEN - 0 12		40		
Input Capacitance	C _{iss}			3174		
Output Capacitance	C _{oss}	$V_{DS} = -50 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		74		pF
Reverse Transfer Capacitance	C_{rss}			70		

Notes

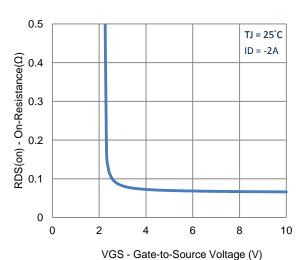
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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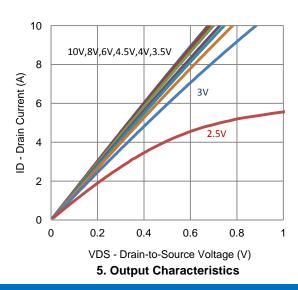
Typical Electrical Characteristics



1. On-Resistance vs. Drain Current



3. On-Resistance vs. Gate-to-Source Voltage



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TJ = 25°C

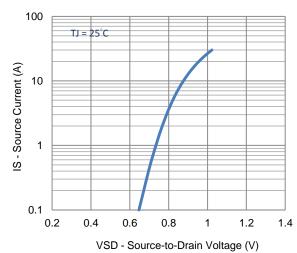
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(V) tuend 6

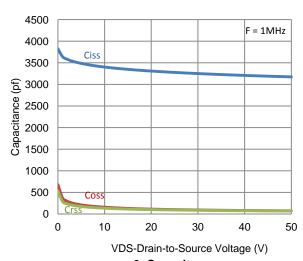
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VGS - Gate-to-Source Voltage (V)

2. Transfer Characteristics

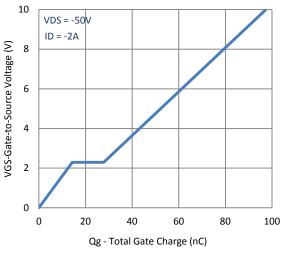


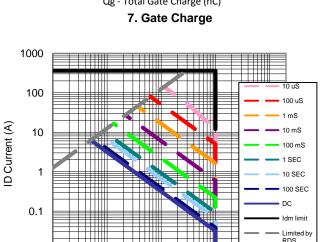
4. Drain-to-Source Forward Voltage



6. Capacitance

Typical Electrical Characteristics





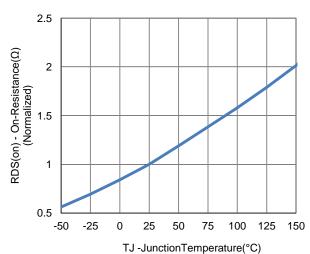
VDS Drain to Source Voltage (V)

9. Safe Operating Area

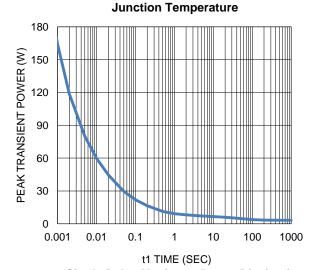
100

1000

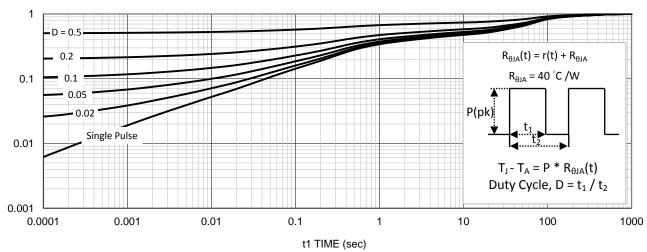
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8. Normalized On-Resistance Vs



10. Single Pulse Maximum Power Dissipation

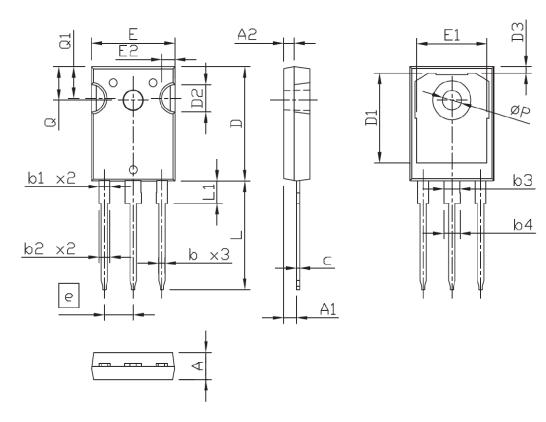


11. Normalized Thermal Transient Junction to Ambient

0.01

0.1

Package Information



	DIMENSIONS IN MILLIMETERS				
SYMBOLS	MIN	NDM	MAX		
Α	4,90	5,00	5,10		
A1	2.32	2.42	2.52		
A2	1,90	2,00	2,10		
b	1.17	1.22	1.27		
b1	1.97	2,02	2.07		
p2	2.00	2.10	2.20		
b3	2.97	3.02	3.07		
b4	3.00	3.10	3.20		
D	0.59	0.62	0.66		
	20,90	21.00	21,10		
D1	16.25	16.55	16.85		
D2		5,00 TYP			
D3	1.05	1.20	1.35		
е		5.44 BS0			
e E	15.70	15.80	15.90		
E1	13.06	13.26	13.46		
E5	2.50 TYP				
Г	19.72	19.92	20.12		
L1			4,30		
Q	6.15 BSC				
Q1	5.60	5,80	6.00		
ØΡ	3.55	3.60	3.65		